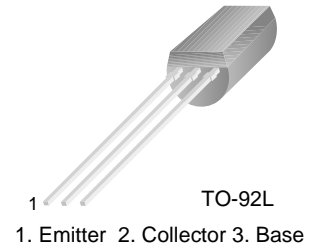


■ ■ APPLICATION: High Voltage Applications.

■ ■ MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_{C}	800	mA
Collector Power Dissipation	P_{C}	1	W
Junction Temperature	T_{J}	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}\text{C}$


■ ■ ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	80		240		$V_{\text{CE}}=5\text{V}, I_{\text{C}}=100\text{mA}$
Collector Cut-off Current	I_{CBO}			0.1	μA	$V_{\text{CB}}=120\text{V}, I_{\text{E}}=0$
Emitter Cut-off Current	I_{EBO}			0.1	μA	$V_{\text{EB}}=5\text{V}, I_{\text{C}}=0$
Collector-Base Breakdown Voltage	BV_{CBO}	120			V	$I_{\text{C}}=1\text{mA}, I_{\text{E}}=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	120			V	$I_{\text{C}}=10\text{mA}, I_{\text{B}}=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	$I_{\text{E}}=1\text{mA}, I_{\text{C}}=0$
Base-Emitter Voltage	V_{BE}			1	V	$V_{\text{CE}}=5\text{V}, I_{\text{C}}=500\text{mA}$
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$			1	V	$I_{\text{C}}=500\text{mA}, I_{\text{B}}=50\text{mA}$
Gain bandwidth product	f_{T}	50	120		MHz	$I_{\text{C}}=100\text{mA}, V_{\text{CE}}=5\text{V}$
Common Base Output Capacitance	C_{ob}			30	pF	$V_{\text{CB}}=10\text{V}, I_{\text{E}}=0, f=1\text{MHz}$

■ ■ h_{FE} Classification And Marking

Classification	O	Y
h_{FE}	80~160	120~240